



VISION OPTO - ELECTRONIC INDUSTRIES

#44-82/1, Tirumala Nagar, Moulali, Hyderabad-500 040.

Tel: +91-40-20086979

Mobile-7306127946

<http://www.visionopto.com>

email : sales@visionopto.com

Chip Material: AlGaInP / GaAs

CODE=RED(S)

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

PARAMETER	SYMBOL	MAXIMUM RATING	UNIT
Power Dissipation	P _D	72	mW
Peak Forward Current (1/10 Duty Cycle, 0.1 Ms Pulse Width)	I _{PEAK}	90	mA
DC Forward Current	I _F	30	mA
Reverse Voltage	V _R	5	V
Operating Temperature Range	T _A	-40°C to +85°C	
Storage Temperature Range	T _{STG}	-40°C to +85°C	
Solder temperature 1/16 inch below seating plane for 3 seconds at 260°C			

ELECTRICAL OPTICAL CHARACTER AND CURVES (Ta = 25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	LOCATION	TEST CONDITION
Forward Voltage	V _F	-	2.10	2.40	V	Per Chip	I _F =20mA
Luminous Intensity	I _v	71.0	75.0	78.0	mcd	Per Chip	I _F =20mA
Peak Emission Wavelength	λ _p	-	645	-	nm	Per Chip	I _F =20mA
Dominant Emission Wavelength	λ _d	626	631	636	nm	Per Chip	I _F =20mA
Spectral Line Half-Width	Δλ _{1/2}	-	20	-	nm	Per Chip	I _F =20mA
Capacitance	C	-	40	-	pF	Per Chip	V _F =0V;f=1MHz
Reverse Current	I _R	-	-	10	uA	Per Chip	V _R = 5V

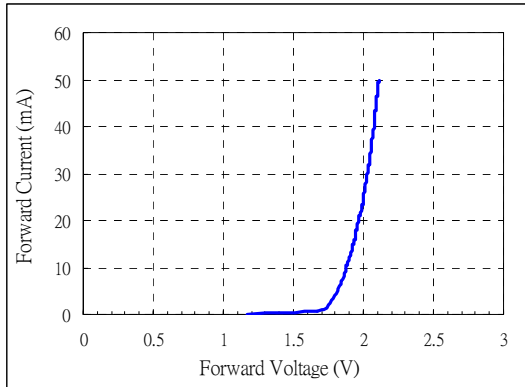
Note: 1. Luminous intensity tolerance is ±10%; 2. Dominant Emission Wavelength tolerance is ±5%.

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Typical Electro-Optical Characteristic Curve:

FIG. 1 Forward Current Vs. Forward Voltage



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G. 2 Relative Intensity Vs. Forward Current

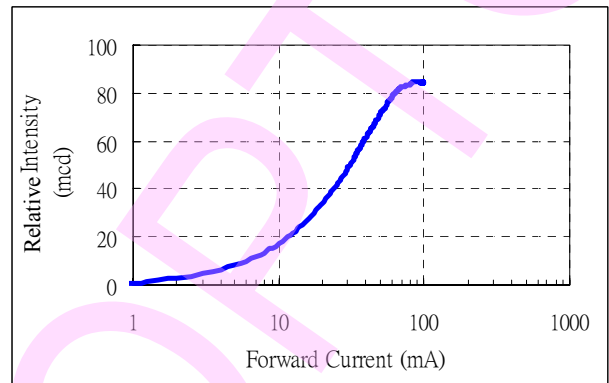
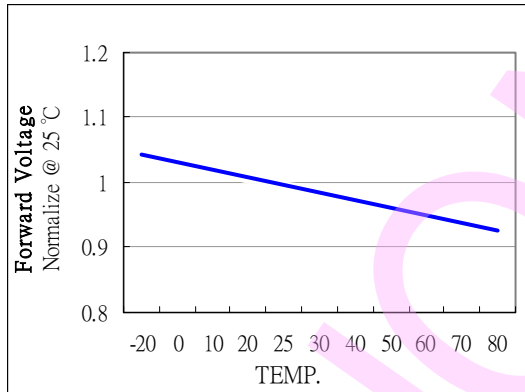


FIG. 3 Forward Voltage Vs. Temperature



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G. 4 Relative Intensity Vs. Temperature

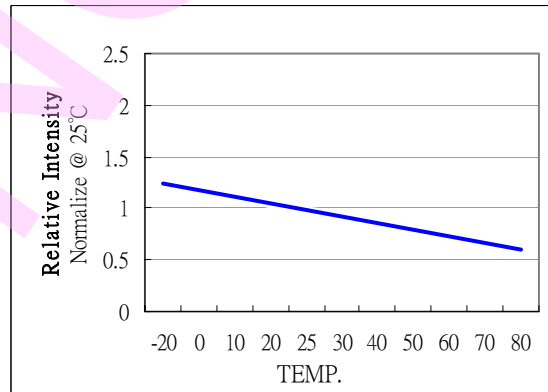


FIG. 5 Relative Intensity Vs. Wavelength

